Quad Bus Buffer

With 5 V-Tolerant Inputs

The MC74LVX125 is an advanced high speed CMOS quad bus buffer. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

The MC74LVX125 requires the 3–state control input (\overline{OE}) to be set High to place the output into the high impedance state.

Features

- High Speed: $t_{PD} = 4.4 \text{ ns}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: $V_{OLP} = 0.5 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V

Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant

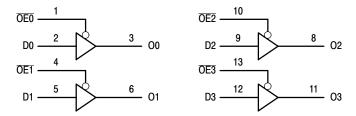


Figure 1. Logic Diagram

PIN NAMES

Pins	Function
OEn Dn On	Output Enable Inputs Data Inputs 3-State Outputs

FUNCTION TABLE

INP	OUTPUTS	
OEn	Dn	On
L	L	L
L	Н	Н
Н	X	Z

 $H=High\ Voltage\ Level;\ L=Low\ Voltage\ Level;\ Z=High\ Impedance\ State;\ X=High\ or\ Low\ Voltage\ Level\ and\ Transitions\ Are\ Acceptable,\ for\ I_{CC}\ reasons,\ DO\ NOT\ FLOAT\ Inputs$



ON Semiconductor®

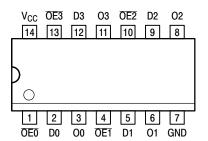
http://onsemi.com





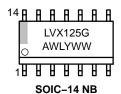
SOIC-14 NB D SUFFIX CASE 751A TSSOP-14 DT SUFFIX CASE 948G

PIN ASSIGNMENT



14-Lead (Top View)

MARKING DIAGRAMS





TSSOP-14

LVX125 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage	–0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation	180	mW
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			v _{cc}		T _A = 25°C	;	$T_A = -40$) to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OH} = -50\mu A$ $I_{OH} = -50\mu A$ $I_{OH} = -4mA$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	I _{OL} = 50μA I _{OL} = 50μA I _{OL} = 4mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l _{in}	Input Leakage Current	V _{in} = 5.5V or GND	3.6			±0.1		±1.0	μΑ
I _{OZ}	Maximum Three–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.25		±2.5	μΑ
I _{CC}	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			4.0		40.0	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns)

					T _A = 25°C		$T_A = -40$) to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay Input to Output	V _{CC} = 2.7V	$C_L = 15pF$ $C_L = 50pF$		5.8 8.3	10.1 13.6	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		4.4 6.9	6.2 9.7	1.0 1.0	8.5 12.0	
t _{PZL} , t _{PZH}	Output Enable Time OE to O	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		5.3 7.8	9.3 12.8	1.0 1.0	12.5 16.0	ns
		$\begin{aligned} &V_{CC} = 3.3 \pm 0.3 V \\ &R_L = 1 k \Omega \end{aligned}$	$C_L = 15pF$ $C_L = 50pF$		4.0 6.5	5.6 9.1	1.0 1.0	7.5 11.0	
t _{PLZ} , t _{PHZ}	Output Disable Time OE to O	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	C _L = 50pF		10.0	15.7	1.0	19.0	ns
		$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	C _L = 50pF		8.3	11.2	1.0	13.0	
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	$C_L = 50pF$ $C_L = 50pF$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

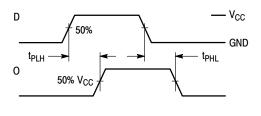
		T _A = 25°C		T _A = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance		6				pF
C _{PD}	Power Dissipation Capacitance (Note 2)		14				pF

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per bit). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

$\textbf{NOISE CHARACTERISTICS} \text{ (Input } t_{r} = t_{f} = 3.0 \text{ns}, \ C_{L} = 50 \text{pF}, \ V_{CC} = 3.3 \text{V}, \ Measured in SOIC Package)}$

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.5	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.5	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

SWITCHING WAVEFORMS



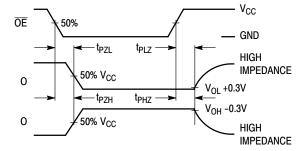
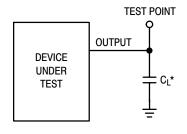
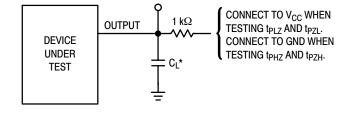


Figure 2.

Figure 3.

TEST CIRCUITS





TEST POINT

*Includes all probe and jig capacitance

Figure 4. Propagation Delay Test Circuit

Figure 5. Three-State Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVX125DG	SOIC-14 NB (Pb-Free)	55 Units / Rail
MC74LVX125DR2G	SOIC-14 NB (Pb-Free)	2500 Tape & Reel
MC74LVX125DTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74LVX125DTR2G	TSSOP-14 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

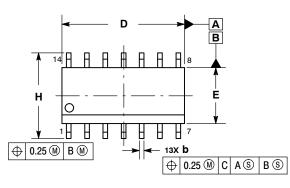
^{*}Includes all probe and jig capacitance

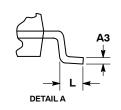


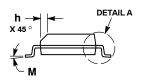


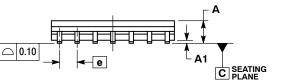
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016









- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE
 MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
Ĺ	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*

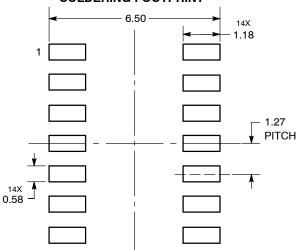


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

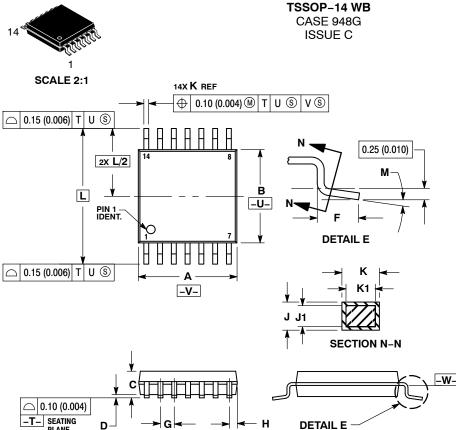
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

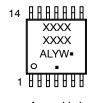
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	° o	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot V = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

0.10 (0.004) T— SEATING PLANE D G G	→ H DETAIL E
SOLDERING	FOOTPRINT
7. 1 1 1 1 1 1 1 1 1 1 2 6 1 1 1 2 6 1	0.65 PITCH

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